



# SPN1423

## N-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPN1423 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

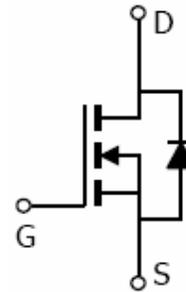
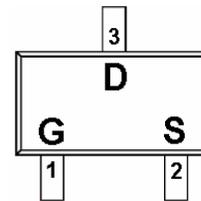
### FEATURES

- ◆ 20V/2.8A,  $R_{DS(ON)} = 90m\Omega @ V_{GS} = 4.5V$
- ◆ 20V/2.2A,  $R_{DS(ON)} = 100m\Omega @ V_{GS} = 2.5V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-323 ( SC-70 ) package design

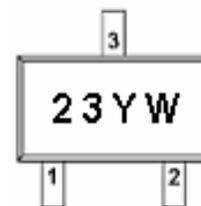
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION ( SOT-323 ; SC-70 )



### PART MARKING



Y : Year Code  
W : Week Code



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### PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPN1423S32RG	SOT-323	23YW

※ Week Code : A ~ Z( 1 ~ 26 ) ; a ~ z( 27 ~ 52 )

※ SPN1423S32RG : Tape Reel ; Pb – Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	VDSS	20	V	
Gate –Source Voltage	VGSS	±12	V	
Continuous Drain Current(Tj=150°C)	ID	TA=25°C	2.8	A
		TA=70°C	2.2	
Pulsed Drain Current	IDM	10	A	
Continuous Source Current(Diode Conduction)	IS	1.6	A	
Power Dissipation	PD	TA=25°C	0.33	W
		TA=70°C	0.21	
Operating Junction Temperature	TJ	150	°C	
Storage Temperature Range	TSTG	-55/150	°C	
Thermal Resistance-Junction to Ambient	RθJA	100	°C/W	



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### ELECTRICAL CHARACTERISTICS

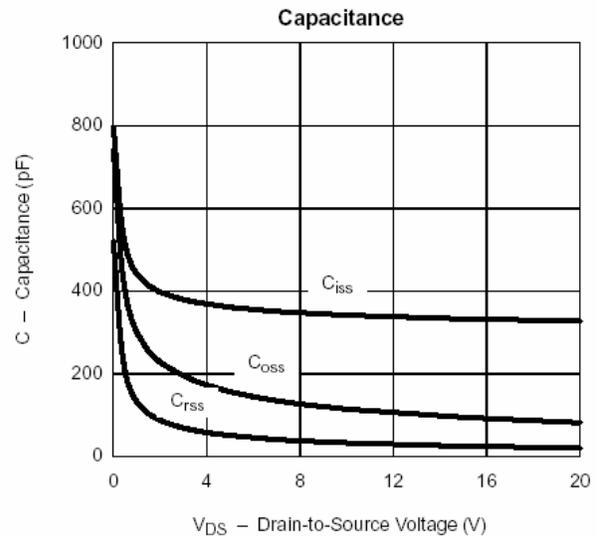
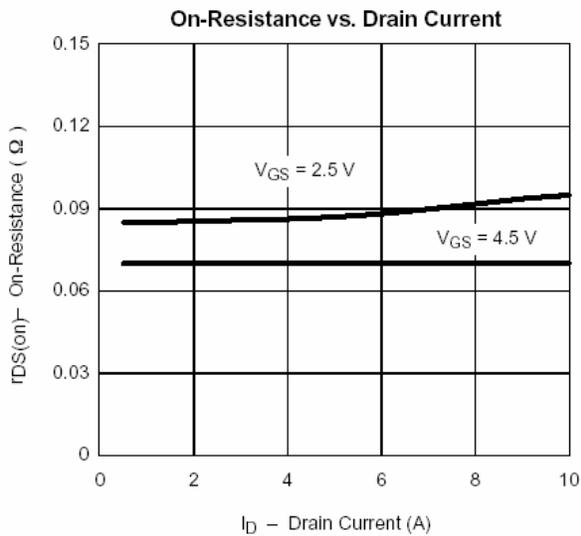
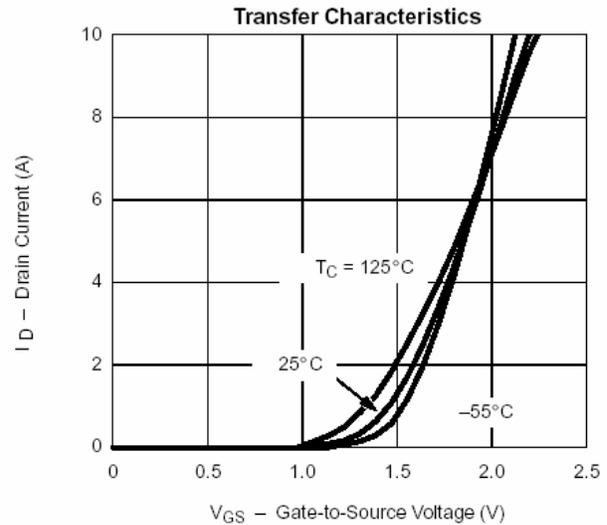
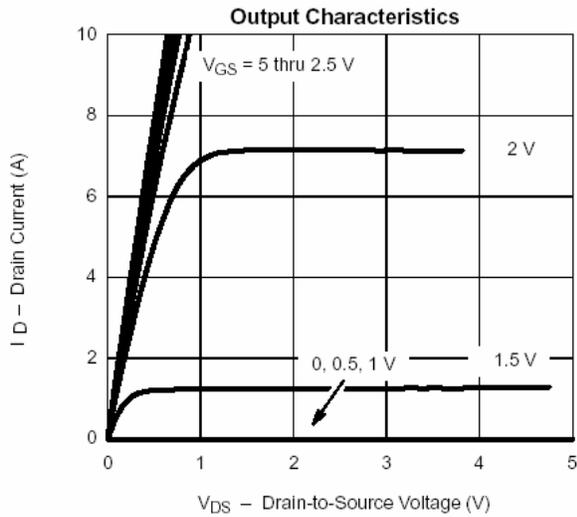
(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45		1.2	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$			1	uA
		$V_{DS}=20V, V_{GS}=0V$ $T_J=55^\circ C$			10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	5			A
		$V_{DS} \geq 5V, V_{GS}=2.5V$	4			
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=2.8A$		0.055	0.090	$\Omega$
		$V_{GS}=2.5V, I_D=2.2A$		0.075	0.100	
Forward Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=2.8A$		10		S
Diode Forward Voltage	$V_{SD}$	$I_S=1.6A, V_{GS}=0V$		0.85	1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=4.5V$ $I_D=2.8A$		5.4	10	nC
Gate-Source Charge	$Q_{gs}$			0.65		
Gate-Drain Charge	$Q_{gd}$			1.4		
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V$ $f=1MHz$		340		pF
Output Capacitance	$C_{oss}$			115		
Reverse Transfer Capacitance	$C_{rss}$			33		
Turn-On Time	$t_{d(on)}$	$V_{DD}=10V, R_L=5.5\Omega$ $I_D=2.8A, V_{GEN}=4.5V$ $R_G=6\Omega$		12	25	ns
	$t_r$			36	60	
Turn-Off Time	$t_{d(off)}$			34	60	
	$t_f$			10	25	



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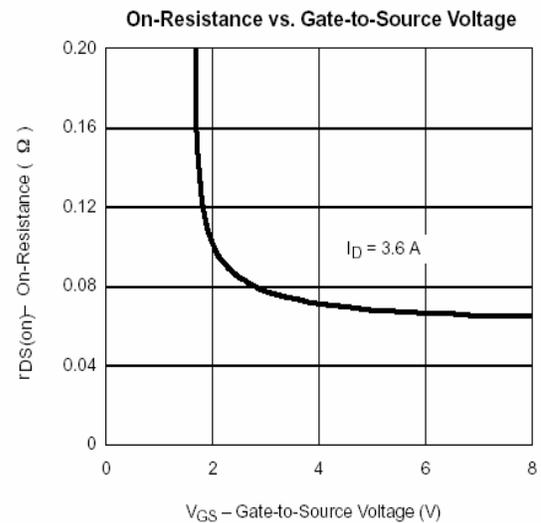
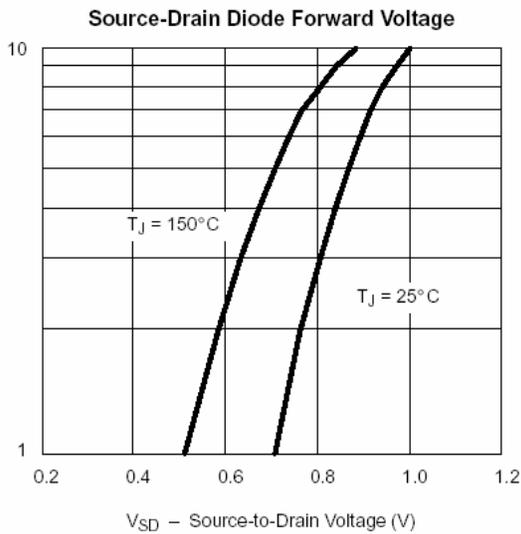
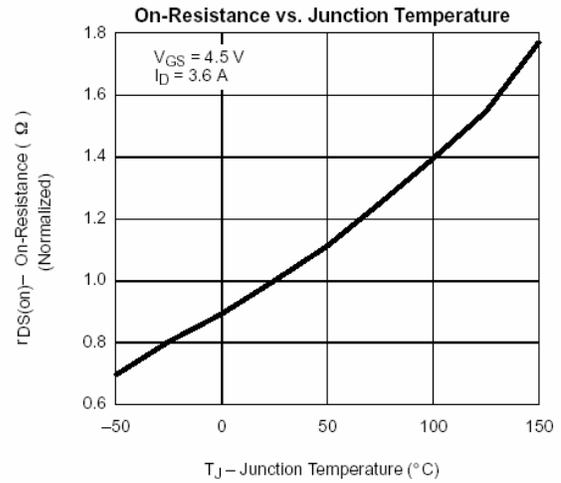
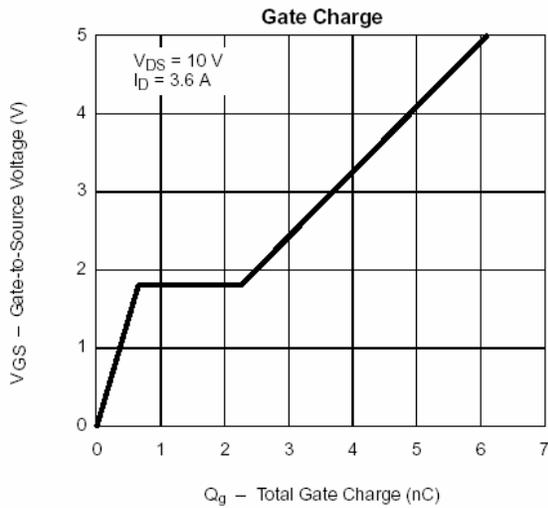
## TYPICAL CHARACTERISTICS





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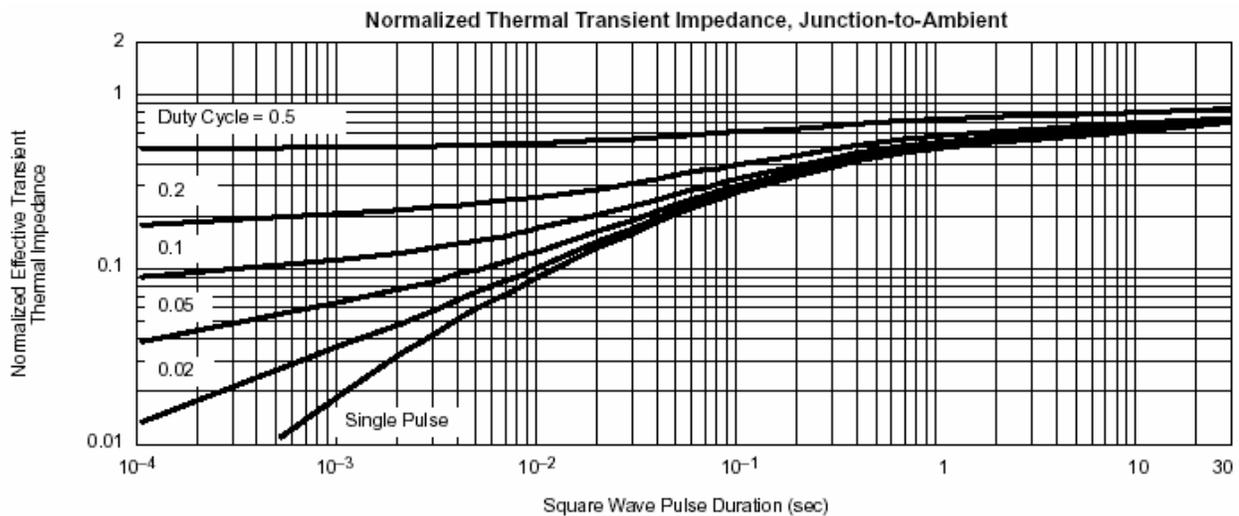
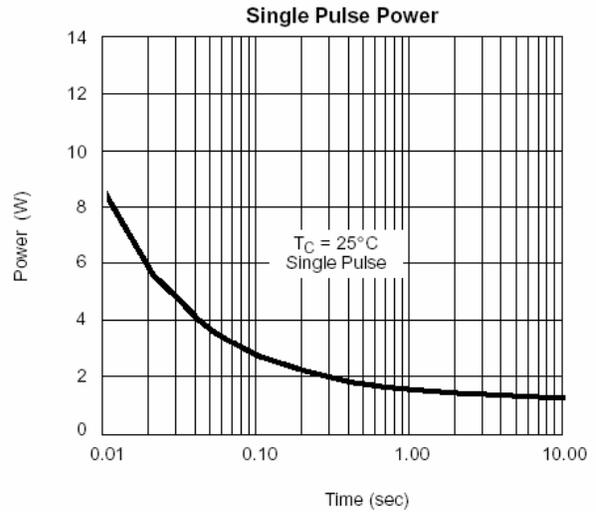
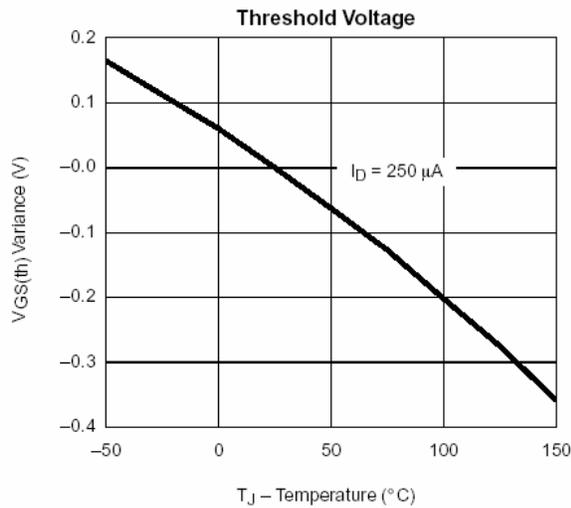
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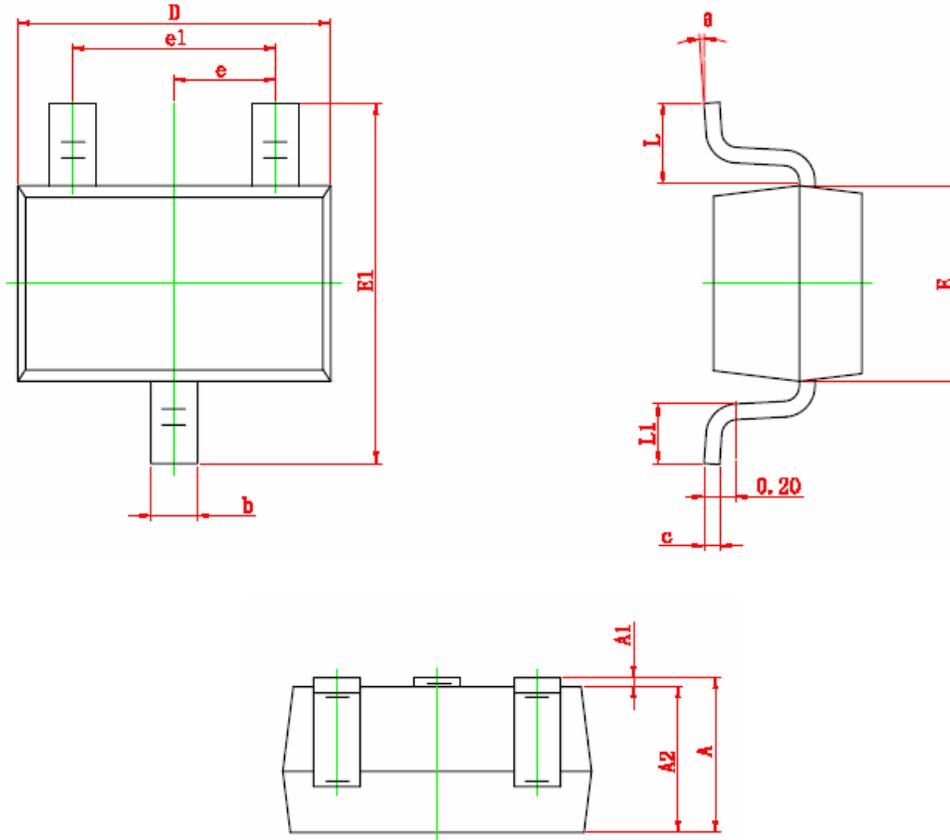
## TYPICAL CHARACTERISTICS





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## SOT-323 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



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SYNC Power Corporation

9F-5, No.3-2, Park Street

NanKang District (NKSP), Taipei, Taiwan 115

Phone: 886-2-2655-8178

Fax: 886-2-2655-8468

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